

isc Silicon PNP Power Transistor

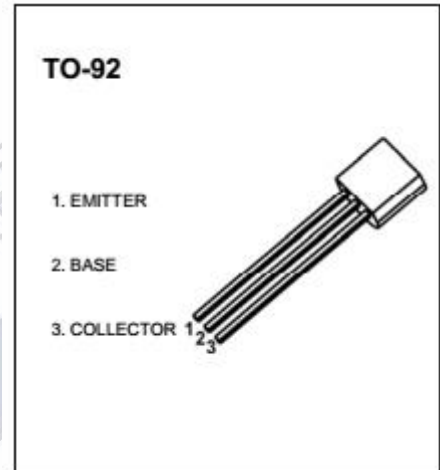
2SA562

DESCRIPTION

- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.

APPLICATIONS

- Designed for high-speed switching and Amplifier applications.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CEB}	Collector-Base Voltage	-35	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _c	Collector Current-Continuous	-0.5	A
P _c	Collector Power Dissipation @T _c =25°C	0.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

isc Silicon PNP Power Transistor**2SA562****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=-100\mu\text{A}, I_E=0$	-35		V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-1\text{mA}, I_B=0$	-30		V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=-100\mu\text{A}, I_C=0$	-5		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=-100\text{mA}; I_B=-10\text{mA}$		-0.25	V
$V_{BE(on)}$	base-emitter voltage	$I_C=-100\text{mA}; V_{CE}=-1\text{V}$		-1.0	V
I_{CBO}	collector cut-off current	$V_{CB}=-35\text{V}, I_E=0$		-0.1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=-5\text{V}; I_C=0$		-0.1	μA
h_{FE-1}	DC Current Gain	$I_C=-0.1\text{A}; V_{CE}=-1\text{V}$	70	240	
h_{FE-2}	DC Current Gain	$I_C=-0.4\text{A}; V_{CE}=-6\text{V}$	25		

Classification of h_{FE1}

Rank	O	Y
h_{FE-1}	70-140	120-240
h_{FE-2}	25min	40min